# TRIPLE DIFFUSED PLANER TYPE HIGH SPEED SWITCHING

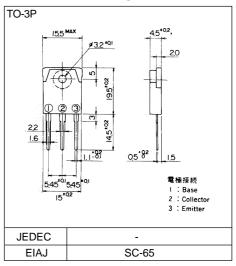
### **■** Features

- High voltage, High speed switching
- Low saturation voltage
- High reliability

## Applications

- Switching regulators
- DC-DC convertor
- Solid State Relay
- General purpose power amplifiers

# ■ Outline Drawings



# ■ Maximum ratings and characteristics

Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Collector-Base voltage	Vсво	250	V
Collector-Emitter voltage	VCEO	200	V
Collector-Emitter voltage	VCEO(SUS)	200	V
Emitter-Base voltage	VEBO	7	V
Collector current	Ic	10	Α
Base current	lв	5	Α
Collector power disspation	Pc	100	W
Operating junction temperature	Tj	+150	℃
Storage temperature	Tstg	-55 to +150	℃

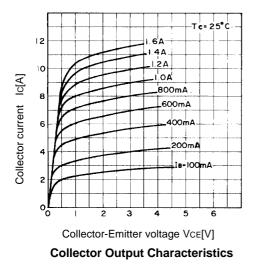
#### ● Electrical characteristics (Tc =25°C unless otherwise specified)

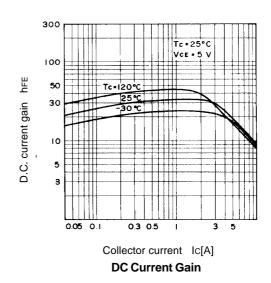
Item	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Collector-Base voltage	Vсво	ICBO = 0.1mA	250			V
Collector-Emitter voltage	VCEO	ICEO = 10mA	200			V
Collector-Emitter voltage	VCEO(SUS)	Ic = 1A	200	-		V
Emitter-Base voltage	VEBO	IEBO = 0.1mA	7	-		V
Collector-Base leakage current	Ісво	VCBO = 250V		-	0.1	mA
Emitter-Base leakage current	<b>I</b> EBO	VEBO = 7V		-	0.1	mA
D.C. current gain	hfE	Ic = 2A, VcE = 5V	20		60	
Collector-Emitter saturation voltage	VCE(Sat)	IC = 2A, IB = 0.8A			0.2	V
Base-Emitter saturation voltage	VBE(Sat)	IC = 5A, IB = 1A			1.1	V
*1	ton	IC = 6A, IB1 = -IB2 = 1.2A			0.8	μs
Switching time	<b>t</b> stg	RL = 10 ohm, Pw = 20µs Duty=<2%			2.0	μs
	tf				0.5	μs

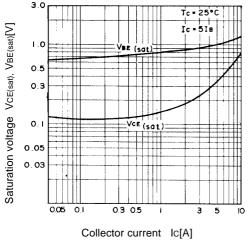
#### Thermal characteristics

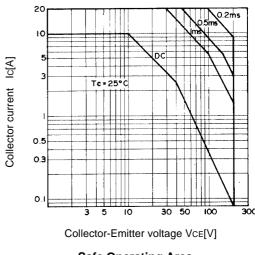
Thermal resistance Rth(j-c) Junction to case 1.25 °C/W	Item	Symbol	Test Conditions	Min.	Тур.	Max.	Units
	Thermal resistance	Rth(j-c)	Junction to case			1.20	°C/W

### Characteristics



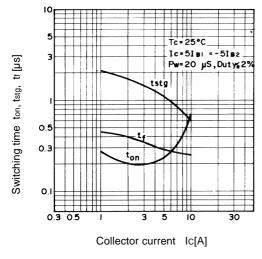






**Base and Collector Saturation Voltage** 





 $R_L = 10 \, \Omega$ 

\*1 Switching Time Test Circuit

**Switching Time**